EMH11 / UMH11N / IMH11A

NPN 100mA 50V Complex Digital Transistors (Bias Resistor Built-in Transistors)

Datasheet

Parameter	Tr1 and Tr2
V_{CC}	50V
I _{C(MAX.)}	100mA
R ₁	10kΩ
R ₂	10kΩ

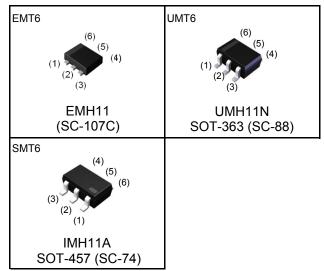
Features

- 1) Built-In Biasing Resistors, $R_1 = R_2 = 10k\Omega$.
- 2) Two DTC114E chips in one package.
- 3) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 4) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

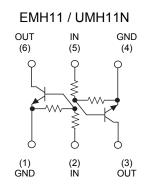
Application

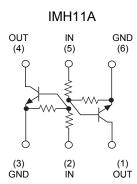
Inverter circuit, Interface circuit, Driver circuit

Outline



●Inner circuit





Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
EMH11	EMT6	1616	T2R	180	8	8,000	H11
UMH11N	UMT6	2021	TN	180	8	3,000	H11
IMH11A	SMT6	2928	T110	180	8	3,000	H11

● Absolute maximum ratings (Ta = 25°C)

<For Tr1 and Tr2 in common>

Param	eter	Symbol	Values	Unit
Supply voltage		V_{CC}	50	V
Input voltage		V_{IN}	-10 to +40	V
Output current		Io	50	mA
Collector current		I _{C(MAX.)} *1	100	mA
Power dissipation EMH11 / UMH11N		P _D *2	150 (Total) ^{*3}	mW
IMH11A		P_{D}	300 (Total) ^{*4}	mW
Junction temperature		T _j	150	°C
Range of storage temperatu	ıre	T _{stg}	−55 to +150	°C

●Electrical characteristics(Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input voltage	$V_{I(off)}$	$V_{CC} = 5V, I_{O} = 100 \mu A$	ı	ı	0.5	V
	$V_{I(on)}$	$V_0 = 0.3V, I_0 = 10mA$	3.0	-	-	V
Output voltage	$V_{O(on)}$	I _O / I _I = 10mA / 0.5mA	-	0.1	0.3	V
Input current	I _I	V _I = 5V	-	-	0.88	mA
Output current	$I_{O(off)}$	$V_{CC} = 50V, V_{I} = 0V$	-	-	0.5	μА
DC current gain	Gı	$V_{\rm O} = 5V, I_{\rm O} = 5mA$	30	-	-	-
Input resistance	R ₁	-	7	10	13	kΩ
Resistance ratio	R ₂ /R ₁	-	0.8	1	1.2	-
Transition frequency	f _T *1	$V_{CE} = 10V, I_{E} = -5mA,$ f = 100MHz	-	250	-	MHz

^{*1} Characteristics of built-in transistor

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^{*2} Each terminal mounted on a reference footprint

^{*3 120}mW per element must not be exceeded.

^{*4 200}mW per element must not be exceeded.

●Electrical characteristic curves (Ta = 25°C)

Fig.1 Input voltage vs. output current (ON characteristics) 100 Vo=0.3V 50 20 INPUT VOLTAGE: V_{I(on)} [V] 10 Ta= -40°C 5 25°C 100°C 500m 200m 100m 5m 10m 20m 50m 100m 100μ 200μ 500μ 1m OUTPUT CURRENT : Io [A]

(OFF characteristics) 10m 5m 2m Ta=100°C OUTPUT CURRENT : I_o [A] 1m **5**00μ 200μ 100μ 50μ 20μ 10μ 5μ 2μ 1μ 3.0 INPUT VOLTAGE : $V_{I(off)}[V]$

Fig.2 Output current vs. input voltage

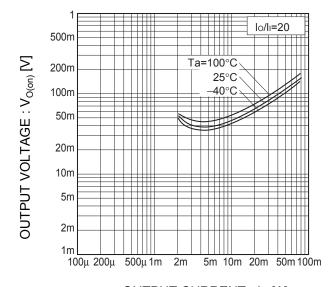
Fig.3 Output current vs. output voltage I_I= 260µA 50 240µA 220µA 40 **OUTPUT CURRENT : I_o [mA]** 200µA DC CURRENT GAIN 180µA 30 160µA 20 140µA 120µA 10 Ta=25°C 100µA 0A 0 0 10 OUTPUT VOLTAGE: Vo [V]

Vo=5V 500 Ta=100°C 25°C 200 40°C 100 50 20 10 5 2 500μ 1m 2m 5m 10m 20m 50m 100m OUTPUT CURRENT : I_O [A]

Fig.4 DC current gain vs. output current

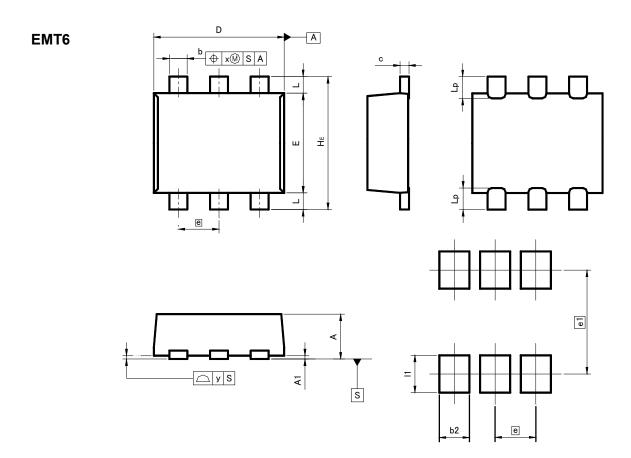
●Electrical characteristic curves (Ta = 25°C)

Fig.5 Output voltage vs. output current



OUTPUT CURRENT : I_0 [A]

●Dimensions (Unit : mm)



Patterm of terminal position areas

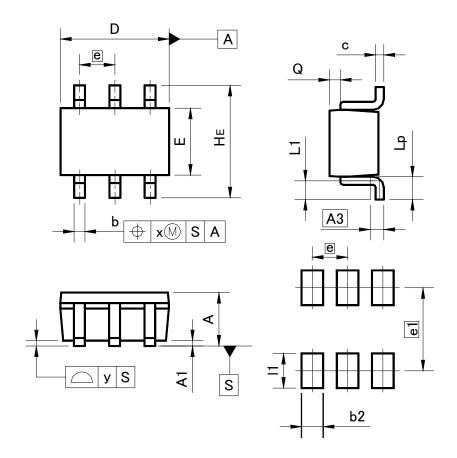
DIM	MILIM	MILIMETERS		HES
DIM	MIN	MAX	MIN	MAX
A1	0.00	0.10	0	0.004
Α	0.45	0.55	0.018	0.022
b	0.17	0.27	0.007	0.011
С	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
E	1.10	1.30	0.043	0.051
е	0.	0.50 0.02		02
HE	1.50	1.70	0.059	0.067
L	0.10	0.30	0.004	0.012
Lp	_	0.35	-	0.014
х	_	0.10		0.004
У	_	0.10	_	0.004

DIM	MILIMETERS		INCHES		
DIM MIN		MAX	MIN	MAX	
e1	1.25		0.049		
b2	_	0.37	_	0.015	
l1	_	0.45	_	0.018	

Dimension in mm/inches

●Dimensions (Unit : mm)

UMT6



Patterm of terminal position areas

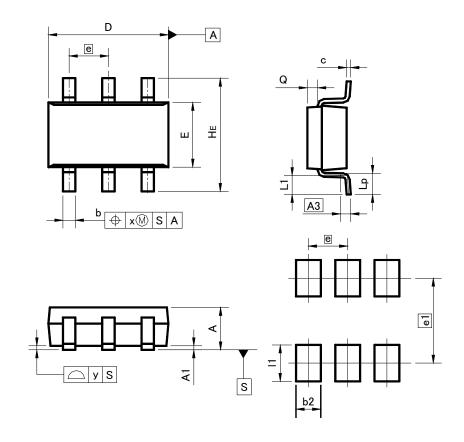
DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	0.80	1.00	1	0.039	
A1	0.00	0.10	0	0.004	
A3	0.2	25	0.0	01	
b	0.15	0.30	0.006	0.012	
С	0.10	0.20	0.004	0.008	
D	1.90	2.10	0.075	0.083	
E	1.15	1.35	0.045	0.053	
е	0.65		0.03		
HE	2.00	2.20	0.079	0.087	
L1	0.20	0.50	0.008	0.02	
Lp	0.25	0.55	0.01	0.022	
Q	0.10	0.30	0.004	0.012	
х	- 1	0.10	1	0.004	
У	-	0.10	1	0.004	

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
e1	1.55		0.06		
b2	-	0.40	ı	0.016	
l1	1	0.65	1	0.026	

Dimension in mm/inches

●Dimensions (Unit : mm)

SMT6



Patterm of terminal position areas

DIM	MILIMETERS		INCHES			
DIM	MIN	MAX	MIN	MAX		
Α	1.00	1.30	0.039	0.051		
A1	0.00	0.10	0	0.004		
A3	0.3	25	0.0	01		
b	0.25	0.40	0.01	0.016		
С	0.09	0.25	0.004	0.01		
D	2.80	3.00	0.11	0.118		
Е	1.50	1.80	0.059	0.071		
е	0.9	0.95		0.95 0.04		04
HE	2.60	3.00	0.102	0.118		
L1	0.30	0.60	0.012	0.024		
Lp	0.40	0.70	0.016	0.028		
Q	0.20	0.30	0.008	0.012		
Х	_	0.20	_	0.008		
У	_	0.10	_	0.004		

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
e1	2.10		0.08		
b2		0.60	1	0.024	
11	_	0.90	ı	0.035	

Dimension in mm/inches

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